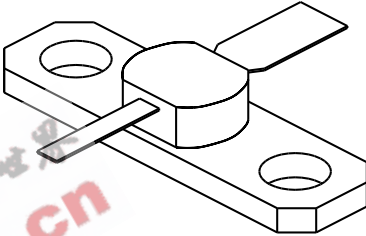


2302

2.0 Watt - 20 Volts, Class C
Microwave 2300 MHz

<p>GENERAL DESCRIPTION The 2302 is a COMMON BASE transistor capable of providing 2 Watts Class C, RF output power at 2300 MHz. Gold metalization and diffused ballasting are used to provide high reliability and supreme ruggedness. The transistor uses a fully hermetic High Temperature Solder Sealed package.</p>	<p>CASE OUTLINE 55 BT- Style 1</p> 
<p>ABSOLUTE MAXIMUM RATINGS</p> <p>Maximum Power Dissipation @ 25°C 7.0 Watts</p> <p>Maximum Voltage and Current</p> <p>BVces Collector to Emitter Voltage 45 Volts BVebo Emitter to Base Voltage 3.5 Volts Ic Collector Current 0.5 Amps</p> <p>Maximum Temperatures</p> <p>Storage Temperature - 65 to + 200°C Operating Junction Temperature + 200°C</p>	

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout	Power Out	F = 2.3 GHz	2.0			Watt
Pin	Power Input	Vcb = 20 Volts			0.3	Watt
Pg	Power Gain	Po = 2.0Watts	8.0	40		dB
η_c	Collector Efficiency	As Above				%
VSWR₁	Load Mismatch Tolerance	F = 2.3 GHz, Po = 2.0W			20:1	

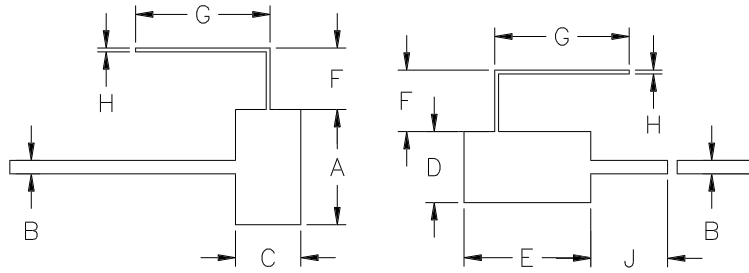
BVces	Collector to Emitter Breakdown	Ic = 10 mA	45			Volts
BVebo	Emitter to Base Breakdown	Ie = 1.0 mA	3.5			Volts
h_{FE}	Current Gain	Vce = 5 V, Ic = 100 mA	10			
Cob	Output Capacitance	F = 1.0 MHz, Vcb = 22 V		4.0		pF
θ_{jc}	Thermal Resistance				25	°C/W

Initial Issue August 1994

GHz TECHNOLOGY INC. RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE. GHz RECOMMENDS THAT BEFORE THE PRODUCT(S) DESCRIBED HEREIN ARE WRITTEN INTO SPECIFICATIONS, OR USED IN CRITICAL APPLICATIONS, THAT THE PERFORMANCE CHARACTERISTICS BE VERIFIED BY CONTACTING THE FACTORY.

REVISIONS

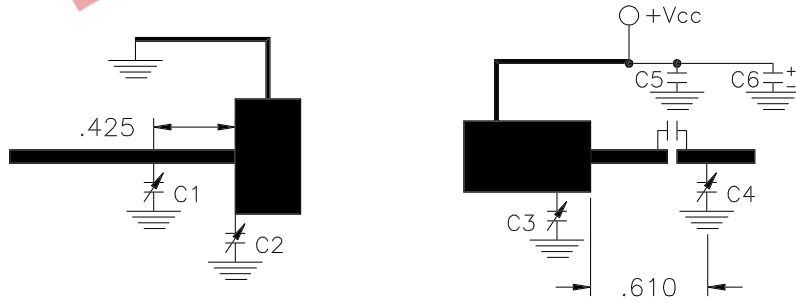
ZONE	REV	DESCRIPTION	DATE	APPROVED
------	-----	-------------	------	----------



DIM	INCHES
A	.600
B	.070
C	.340
D	.370
E	.650
F	.320
G	.700
H	.020
J	.400

EEPW 电子产品世界 .com.cn

2302 TEST CIRCUIT



MICROSTRIP $t = 0.020''$
 C1,C2,C3,C4 = 0.3-3.5Pf
 C5 = 0.1ufd
 C6 = 4.7ufd 50V